

CONTEXT & MOTIVATION

Magnetic Tunnel Junction (MTJ) is suitable for a wide range of applications

Physical Unclonable Function (PUF)

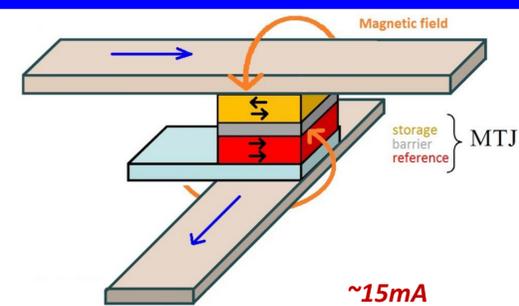
Magnetic Tunnel Junction (MTJ) is suitable for two main hardware security applications

True Random Number Generator (TRNG)

- Physical Unclonable Function (PUF)
 - Application
 - Secure authentication
 - Manufacturing variability
 - Variability of electrical resistance of MTJ
- True Random Number Generator (TRNG)
 - Application
 - Random cryptographic keys
 - Statistical sampling
 - Advanced simulation techniques
 - Source of randomness from STT-MRAM
 - Stochastic nature of STT switching

MAGNETIC RANDOM ACCESS MEMORY (MRAM) TECHNOLOGIES

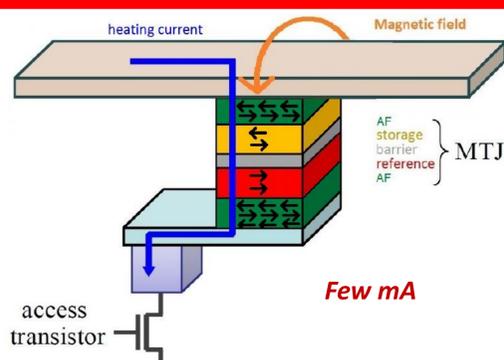
Field Induced Magnetic Switching (FIMS)



~15mA

- First MRAM generation
- Two combined magnetic fields may flip the free layer magnetization

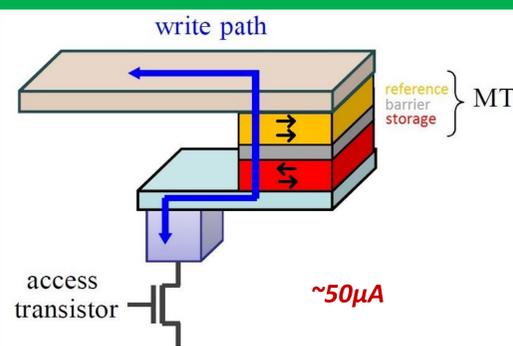
Thermally Assisted Switching (TAS)



Few mA

- FM layers' magnetization is blocked at room temp.
- Heating the junction unblocks the free layer

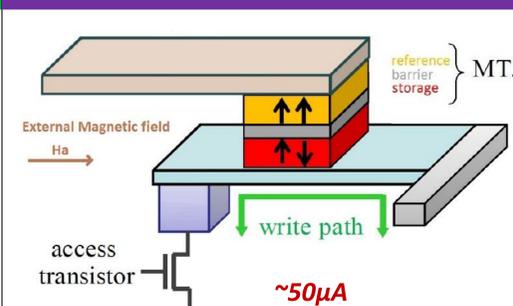
Spin Transfer Torque (STT)



~50µA

- Spin-polarized current can flip the free layer
- No external magnetic field needed
- Shared read/write path

Spin Orbit Torque (SOT)



~50µA

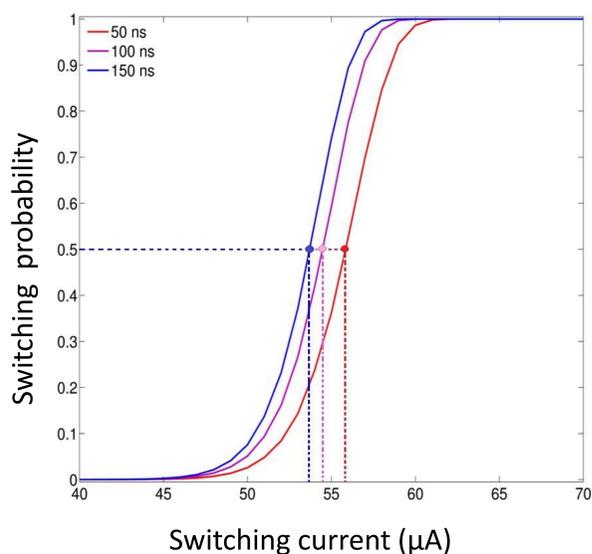
- SOT switching is currently not fully understood
- Separated read/write path

MRAM-BASED SECURE DEVICES

MRAM-based TRNG Principle

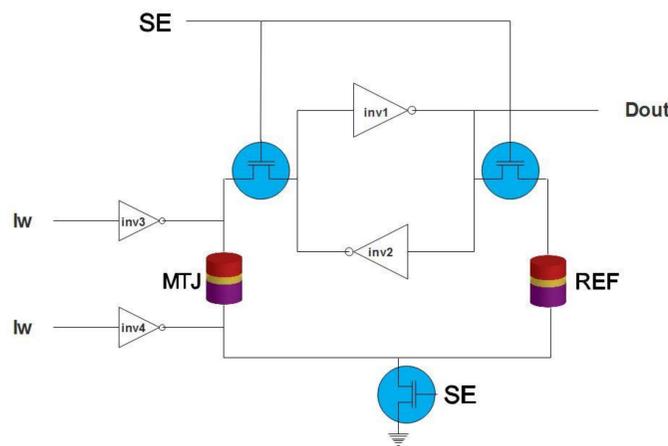
TRNG principle

- STT-MRAM switching is stochastic dependent and probabilistic
- The switching probability depends on:
 - Writing current value
 - Writing pulse time

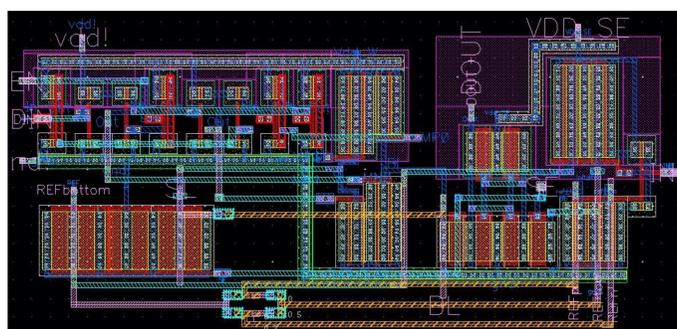


MRAM-based TRNG basic cells

TRNG VLSI structure

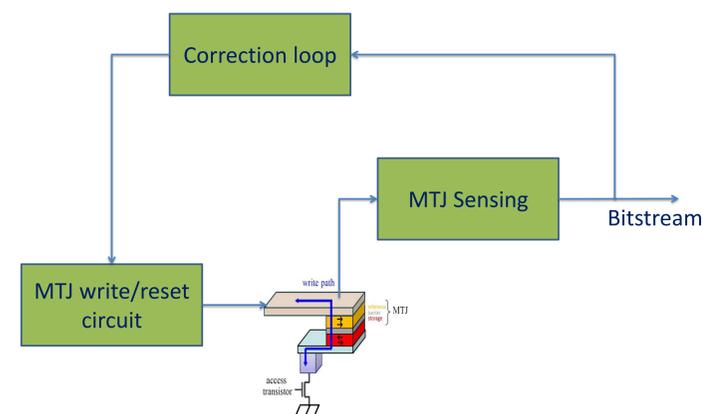


TRNG circuit



MRAM-based TRNG with feedback

TRNG Control feedback



- Correction loop will act on writing current or writing pulse time
- Generate accurate random bitstream in standalone